

MOSFET – N-Channel, SUPERFET[®], FRFET[®]

600 V, 11 A, 380 mΩ

FCPF11N60F

Description

SUPERFET MOSFET is onsemi's first generation of high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This technology is tailored to minimize conduction loss, provide superior switching performance, dv/dt rate and higher avalanche energy. Consequently, SUPERFET MOSFET is very suitable for the switching power applications such as PFC, server/telecom power, FPD TV power, ATX power and industrial power applications. SUPERFET FRFET MOSFET's optimized body diode reverse recovery performance can remove additional component and improve system reliability.

Features

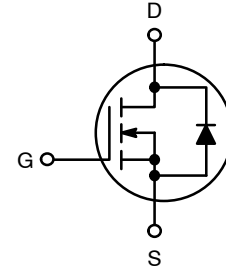
- 600 V @ $T_J = 150^{\circ}\text{C}$
- $R_{DS(on)} = 320\text{ m}\Omega$ (Typ.)
- Fast Recovery Type ($t_{rr} = 120\text{ ns}$)
- Ultra Low Gate Charge (Typ. $Q_g = 40\text{ nC}$)
- Low Effective Output Capacitance (Typ. $C_{oss(eff.)} = 95\text{ pF}$)
- 100% Avalanche Tested
- These Devices are Pb-Free and are RoHS Compliant

Applications

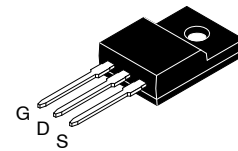
- LCD/LED/PDP TV
- Lighting
- Solar Inverter
- AC-DC Power Supply

V_{DS}	$R_{DS(on)}\text{ MAX}$	$I_D\text{ MAX}$
600 V	380 mΩ @ 10 V	11 A*

*Drain current limited by maximum junction temperature.

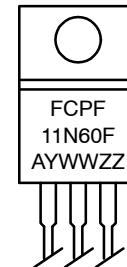


N-Channel



TO-220 FULLPAK, 3-Lead
/ TO-220F-3SG
CASE 221AT

MARKING DIAGRAM



FCPF11N60F = Specific Device Code
A = Assembly Location
YWW = Date Code (Year & Week)
ZZ = Assembly Lot

ORDERING INFORMATION

Device	Package	Shipping
FCPF11N60F	TO-220-3 FULLPAK	1000 Units / Tube

FCPF11N60F

MOSFET MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter		FCPF11N60F	Unit
V_{DSS}	Drain to Source Voltage		600	V
I_D	Drain Current	– Continuous ($T_C = 25^\circ\text{C}$)	11*	A
		– Continuous ($T_C = 100^\circ\text{C}$)	7*	
I_{DM}	Drain Current	– Pulsed (Note 1)	33*	A
V_{GSS}	Gate to Source Voltage		± 30	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)		340	mJ
I_{AR}	Avalanche Current (Note 1)		11	A
E_{AR}	Repetitive Avalanche Energy (Note 1)		12.5	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		4.5	V/ns
P_D	Power Dissipation	($T_C = 25^\circ\text{C}$)	36	W
		– Derate Above 25°C	0.29	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to $+150$	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds		300	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

*Drain current limited by maximum junction temperature.

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. $I_{AS} = 5.5$ A, $V_{DD} = 50$ V, $R_G = 25$ Ω , starting $T_J = 25^\circ\text{C}$.
3. $I_{SD} \leq 11$ A, $di/dt \leq 200$ A/ μs , $V_{DD} \leq BV_{DSS}$, starting $T_J = 25^\circ\text{C}$.

THERMAL CHARACTERISTICS

Symbol	Parameter	FCPF11N60F	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	3.5	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	$^\circ\text{C/W}$

FCPF11N60F

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

BV _{DSS}	Drain to Source Breakdown Voltage	V _{GS} = 0 V, I _D = 250 μA , T _C = 25°C	600	–	–	V
		V _{GS} = 0 V, I _D = 250 μA , T _C = 150°C	–	650	–	V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I _D = 250 μA , Referenced to 25°C	–	0.6	–	V/°C
BV _{DS}	Drain–Source Avalanche Breakdown Voltage	V _{GS} = 0 V, I _D = 11 A	–	700	–	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 600 V, V _{GS} = 0 V	–	–	1	μA
		V _{DS} = 480 V, T _C = 125°C	–	–	10	
I _{GSS}	Gate to Body Leakage Current	V _{GS} = ± 30 V, V _{DS} = 0 V	–	–	± 100	nA

ON CHARACTERISTICS

V _{GS(th)}	Gate Threshold Voltage	V _{GS} = V _{DS} , I _D = 250 μA	3.0	–	5.0	V
R _{DS(on)}	Static Drain to Source On–Resistance	V _{GS} = 10 V, I _D = 5.5 A	–	0.32	0.38	Ω
g _{FS}	Forward Transconductance	V _{DS} = 40 V, I _D = 5.5 A	–	6	–	S

DYNAMIC CHARACTERISTICS

C _{iss}	Input Capacitance	V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz	–	1148	1490	pF
C _{oss}	Output Capacitance		–	671	870	pF
C _{rss}	Reverse Transfer Capacitance		–	63	82	pF
C _{oss}	Output Capacitance	V _{DS} = 480 V, V _{GS} = 0 V, f = 1 MHz	–	35	–	pF
C _{oss(eff.)}	Effective Output Capacitance	V _{DS} = 0 V to 400 V, V _{GS} = 0 V	–	95	–	pF
Q _{g(tot)}	Total Gate Charge at 10 V	V _{DS} = 480 V, I _D = 11 A, V _{GS} = 10 V (Note 4)	–	40	52	nC
Q _{gs}	Gate to Source Gate Charge		–	7.2	–	nC
Q _{gd}	Gate to Drain “Miller” Charge		–	21	–	nC

SWITCHING CHARACTERISTICS

t _{d(on)}	Turn–On Delay Time	V _{DD} = 300 V, I _D = 11 A, R _G = 25 Ω (Note 4)	–	34	80	ns
t _r	Turn–On Rise Time		–	98	205	ns
t _{d(off)}	Turn–Off Delay Time		–	119	250	ns
t _f	Turn–Off Fall Time		–	56	120	ns

DRAIN–SOURCE DIODE CHARACTERISTICS

I _S	Maximum Continuous Drain to Source Diode Forward Current		–	–	11	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		–	–	33	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0 V, I _{SD} = 11 A	–	–	1.4	V
t _{rr}	Reverse Recovery Time		–	120	–	ns
Q _{rr}	Reverse Recovery Charge		–	0.8	–	μC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Essentially independent of operating temperature

TYPICAL PERFORMANCE CHARACTERISTICS

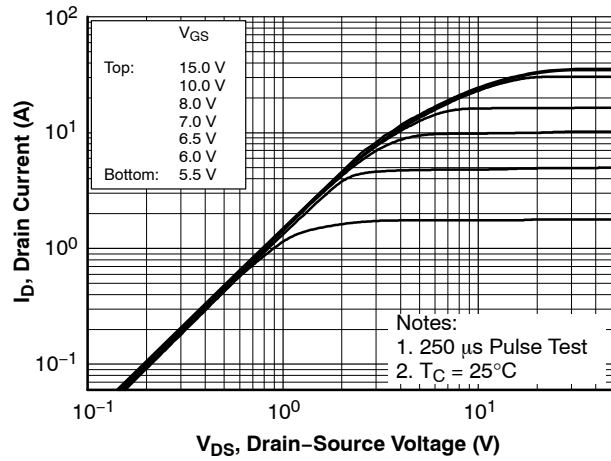


Figure 1. On-Region Characteristics

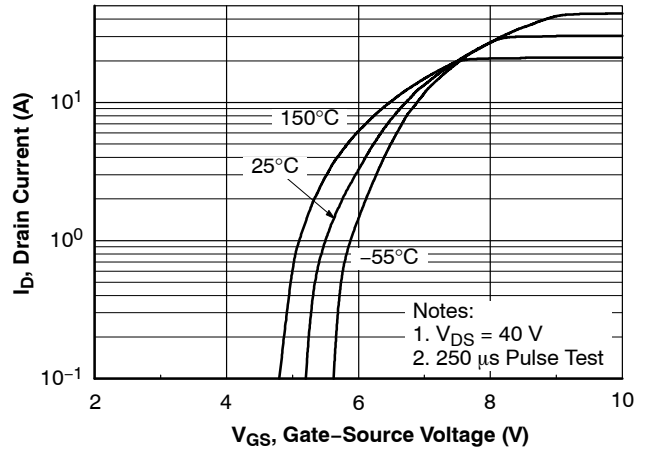


Figure 2. Transfer Characteristics

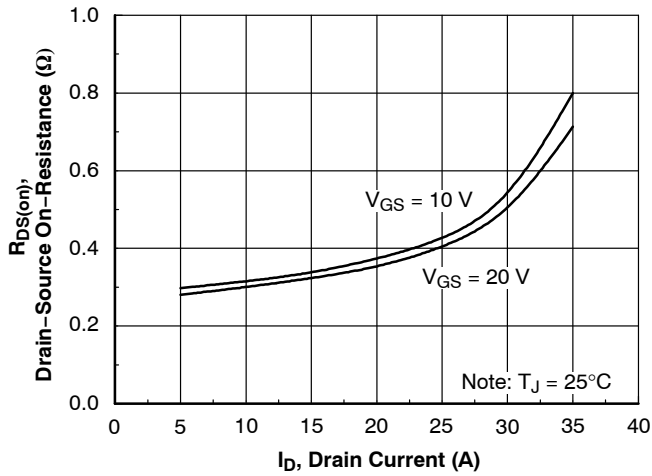


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

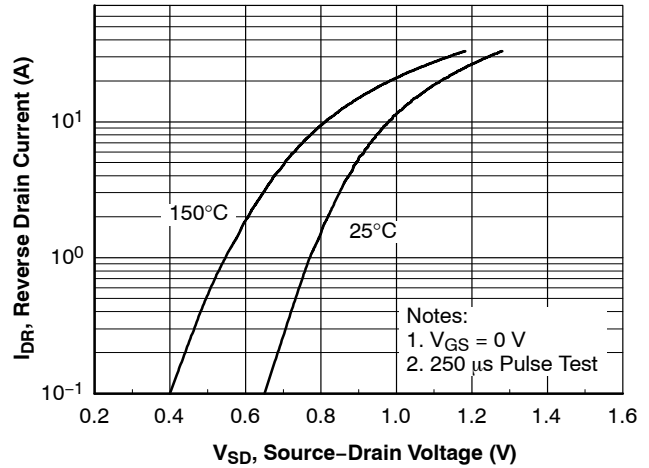


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

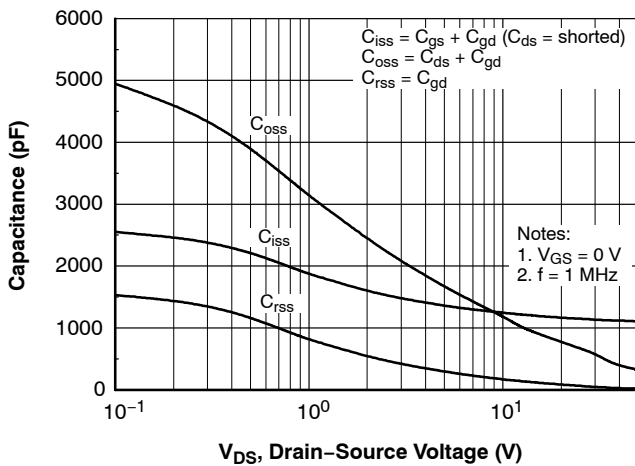


Figure 5. Capacitance Characteristics

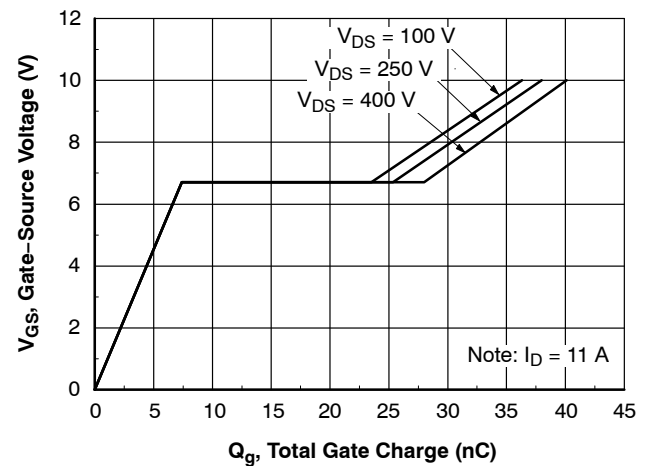


Figure 6. Gate Charge Characteristics

TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

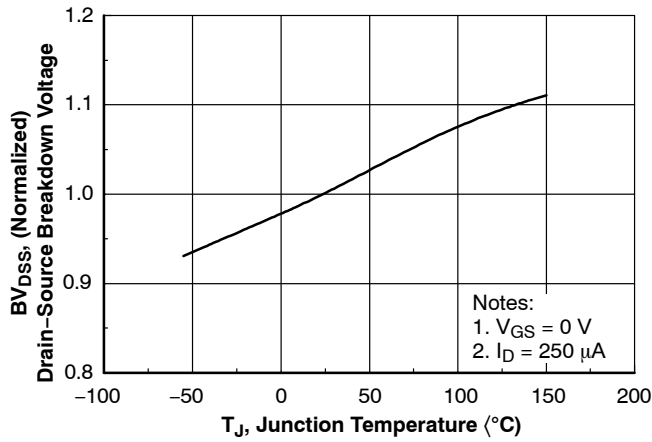


Figure 7. Breakdown Voltage Variation vs. Temperature

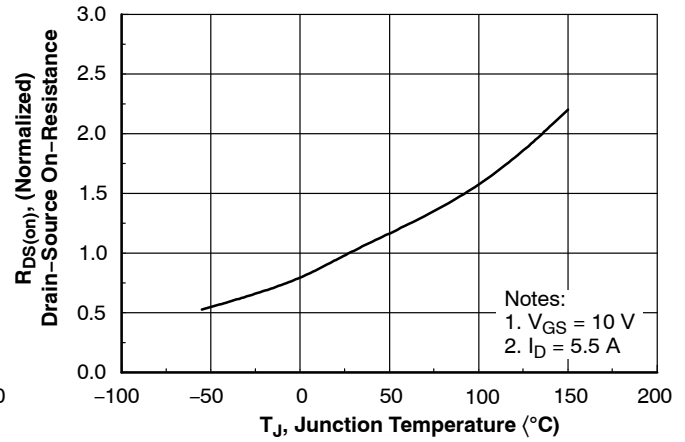


Figure 8. On-Resistance Variation vs. Temperature

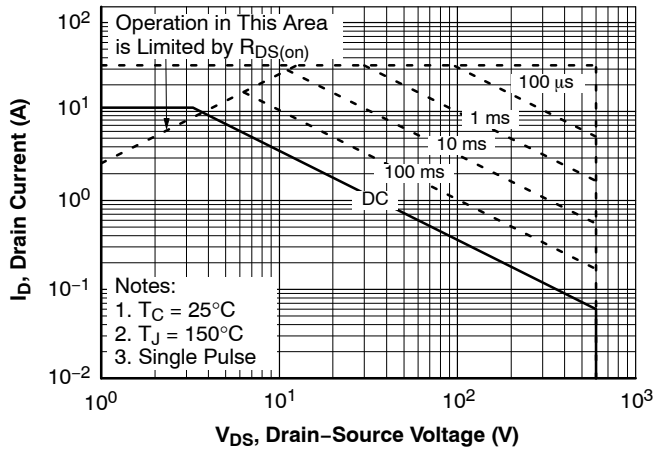


Figure 9. Safe Operating Area

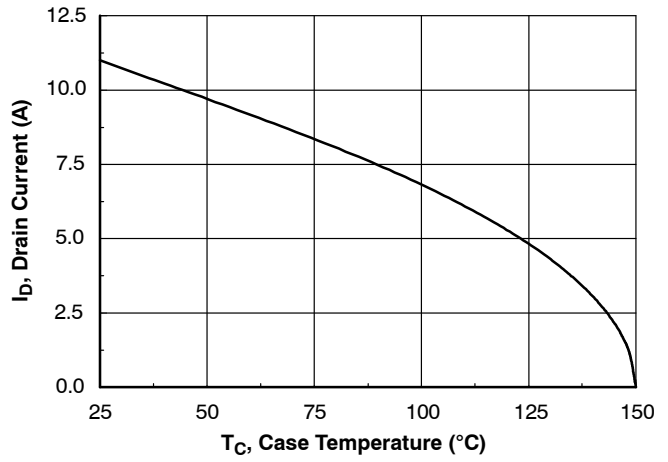


Figure 10. Maximum Drain Current vs. Case Temperature

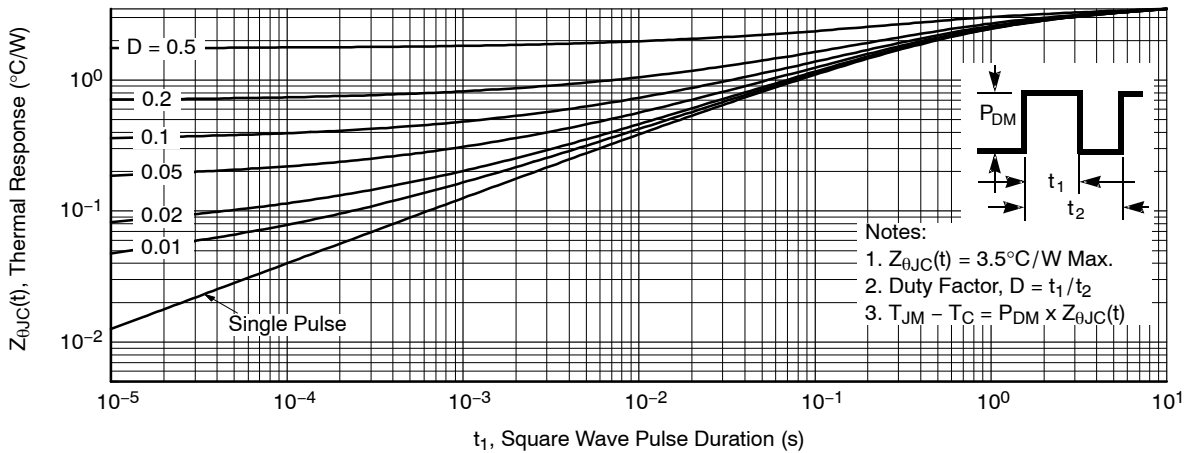
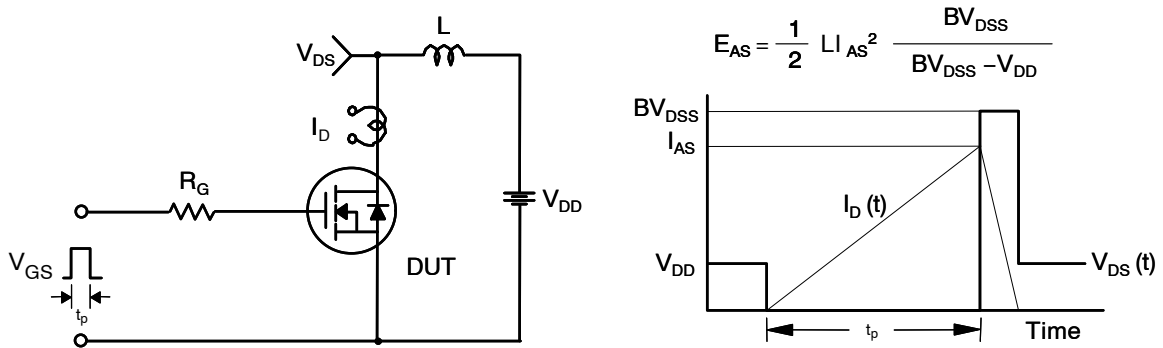
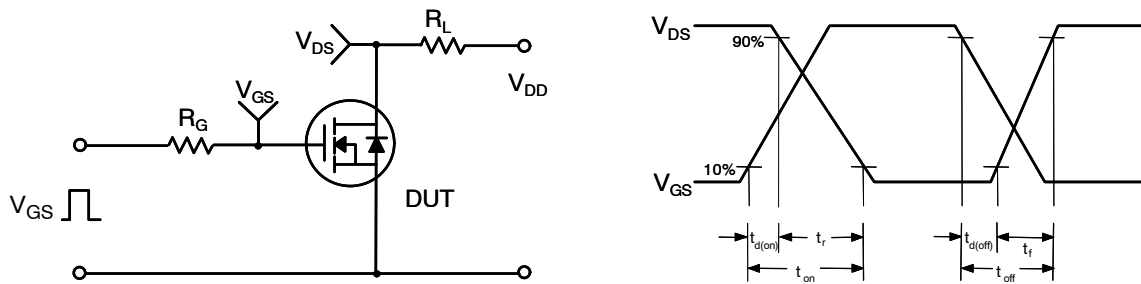
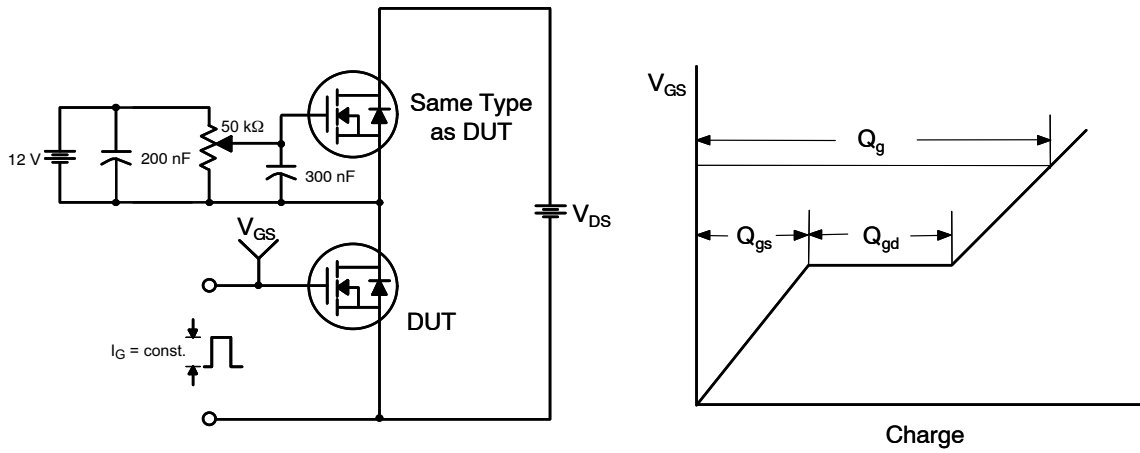


Figure 11. Transient Thermal Response Curve

FCPF11N60F



FCPF11N60F

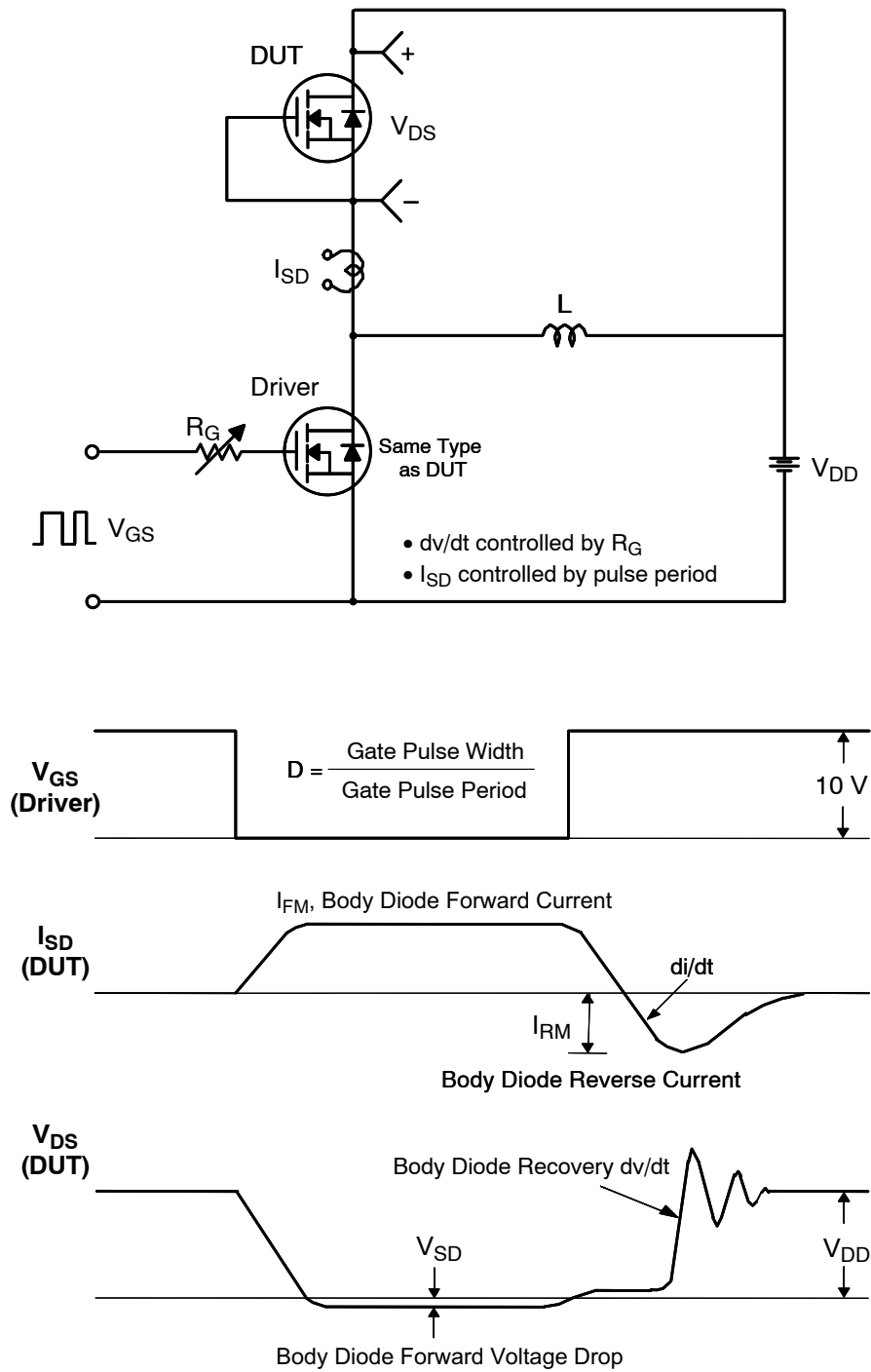
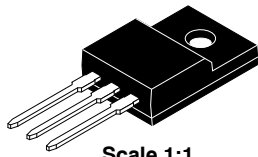


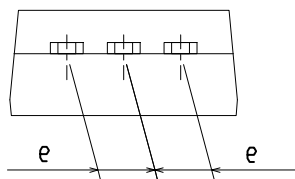
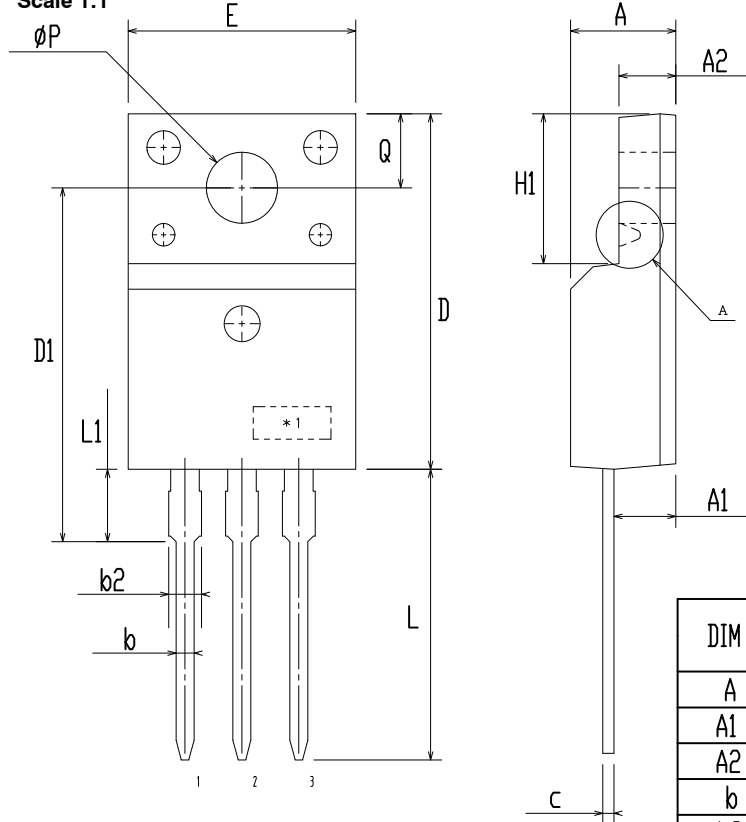
Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

TO-220 Fullpack, 3-Lead / TO-220F-3SG
CASE 221AT
ISSUE B

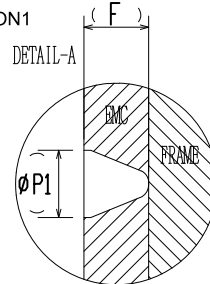
DATE 19 JAN 2021



Scale 1:1



OPTION1



DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.50	4.70	4.90
A1	2.56	2.76	2.96
A2	2.34	2.54	2.74
b	0.70	0.80	0.90
b2	~	~	1.47
c	0.45	0.50	0.60
D	15.67	15.87	16.07
D1	15.60	15.80	16.00
E	9.96	10.16	10.36
e	2.34	2.54	2.74
F	~	0.84	~
H1	6.48	6.68	6.88
L	12.78	12.98	13.18
L1	3.03	3.23	3.43
Ø P	2.98	3.18	3.38
Ø P1	~	1.00	~
Q	3.20	3.30	3.40

NOTES:

A. DIMENSION AND TOLERANCE AS ASME Y14.5-2009

B. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUCTIONS.

C. OPTION 1 - WITH SUPPORT PIN HOLE

OPTION 2 - NO SUPPORT PIN HOLE

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DESCRIPTION:	TO-220 FULLPACK, 3-LEAD / TO-220F-3SG	PAGE 1 OF 1

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